

Supplementary Information

N-type and p-type molecular doping on monolayer MoS₂

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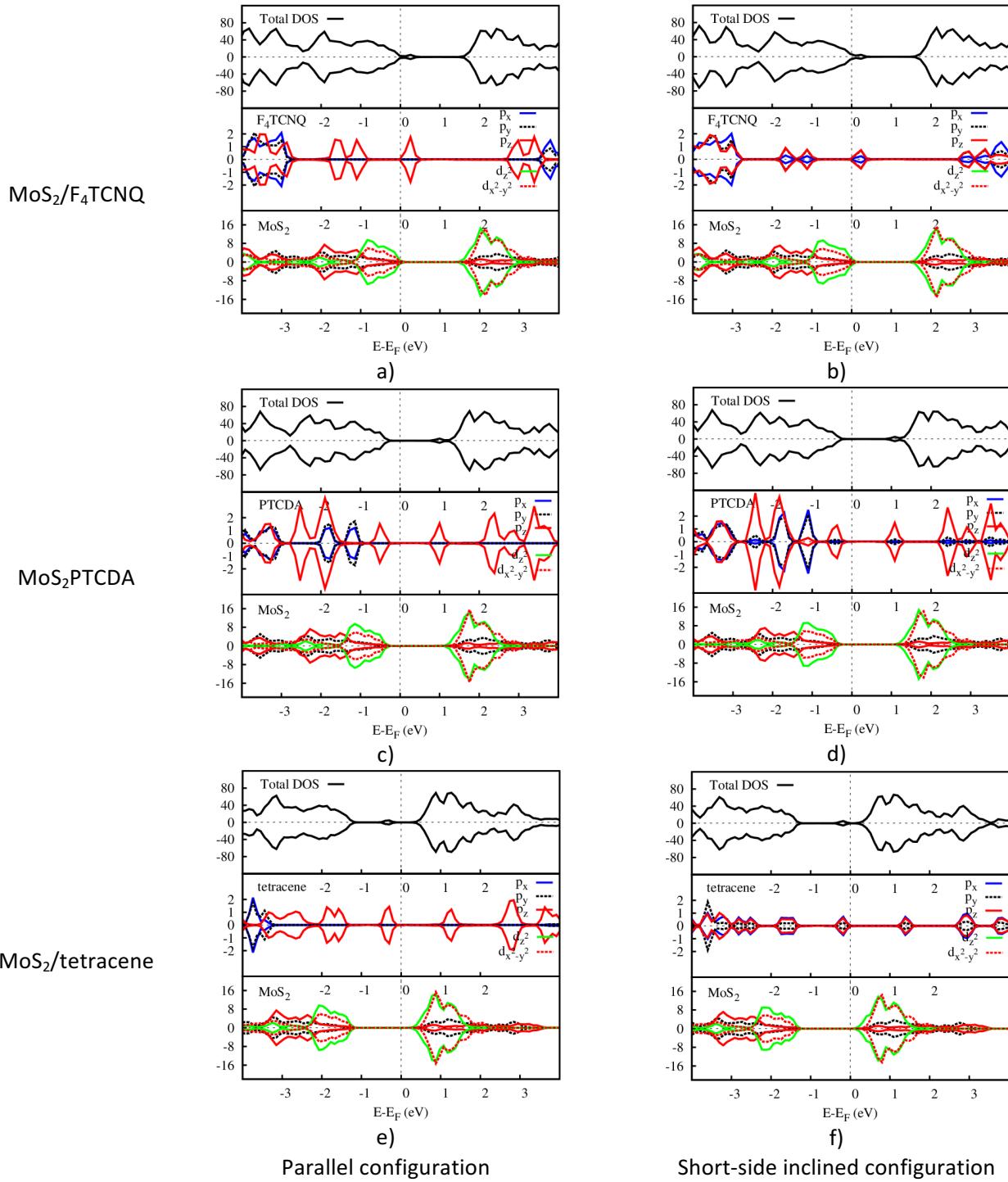


Fig. S1 Electronic density of states of $\text{MoS}_2/\text{F}_4\text{TCNQ}$, $\text{MoS}_2/\text{PTCDA}$, and $\text{MoS}_2/\text{tetracene}$ for the most favorable configuration (the short-side inclined) and the parallel configuration. The DOS is almost the same for the parallel and short-side inclined configurations.

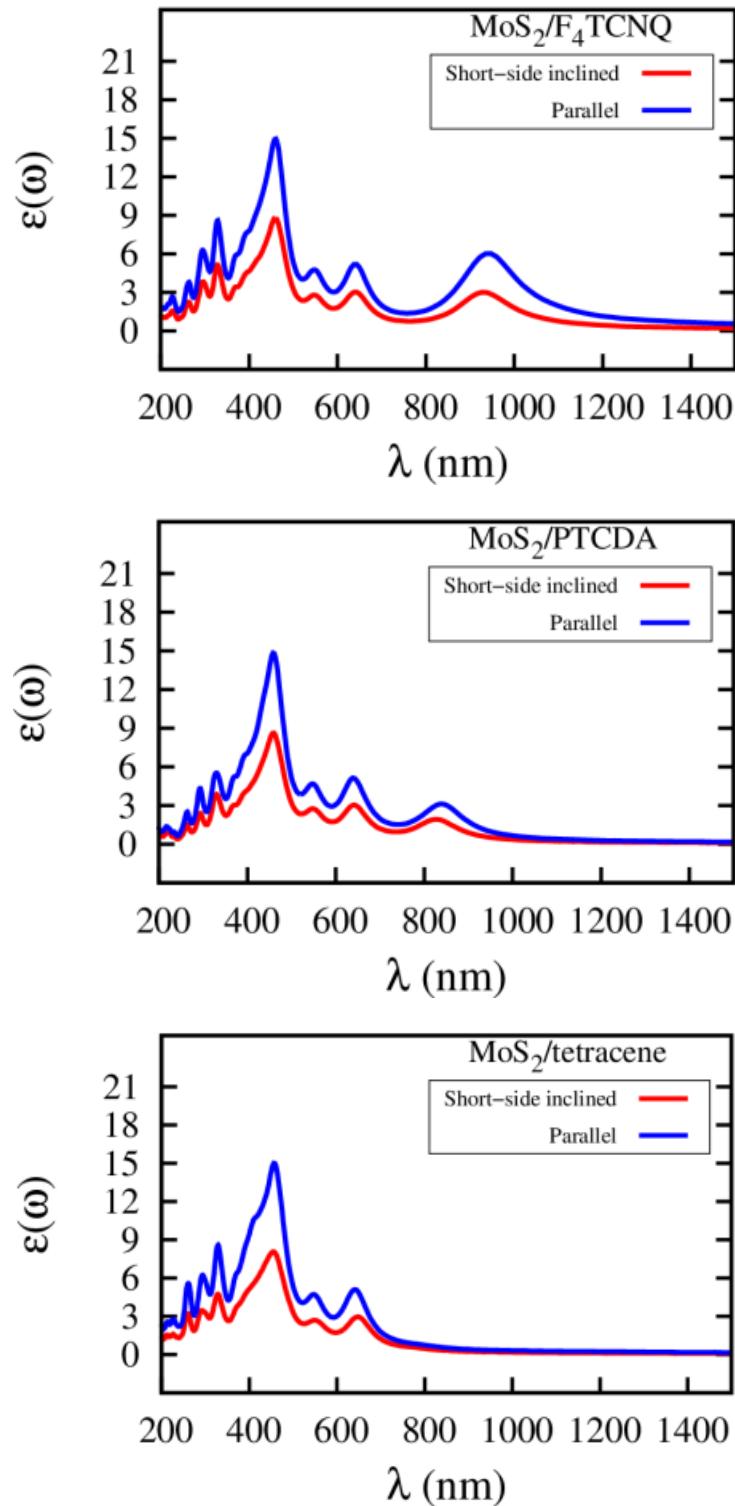


Fig. S2 Imaginary part of dielectric function $\epsilon(\omega)$ versus wavelength λ for MoS₂/F₄TCNQ, MoS₂/PTCDA, and MoS₂/tetracene at zero pressure for different configurations and vacuum spaces.

Table S1 The adsorption energy (eV) of the molecules on the monolayer MoS₂.

Unit cell	MoS₂/F₄TCNQ	MoS₂/PTCDA	MoS₂/tetracene
5x5	-0.009	0.019	0.039
6x6	-0.028	-0.010	0.008

Table S2 The adsorption energy (eV) of the molecules on the monolayer MoS₂ with and without the inclusion of van der Waals dispersion correction.

Functional	F₄TCNQ	PTCDA	tetracene
Without vdW (PBE)	-0.009	0.019	0.039
vdW-DF (revPBE)*	-1.109	-1.664	-1.205

* M. Dion, H. Rydberg, E. Schröder, D. C. Langreth, B. I. Lundqvist, Phys. Rev. Lett. 92, 246401 (2004)

Table S3 The bandgap E_g (eV) of MoS₂/F₄TCNQ, MoS₂/PTCDA, and MoS₂/tetracene systems with and

Functional	Isolated MoS₂	F₄TCNQ	PTCDA	tetracene
Without vdW (PBE)	1.68	0.36	1.43	0.72
vdW-DF (revPBE)*	1.70	0.40	1.45	0.60

without the van der Waals dispersion correction.

The adsorption energy for a larger unit cell size and with van der Waals correction is more negative than the 5 x 5 unit cell without vdW correction. However, the DOS remains the same for all of them (see Fig. S3). The inclusion of vdW correction slightly modifies the bandgap.

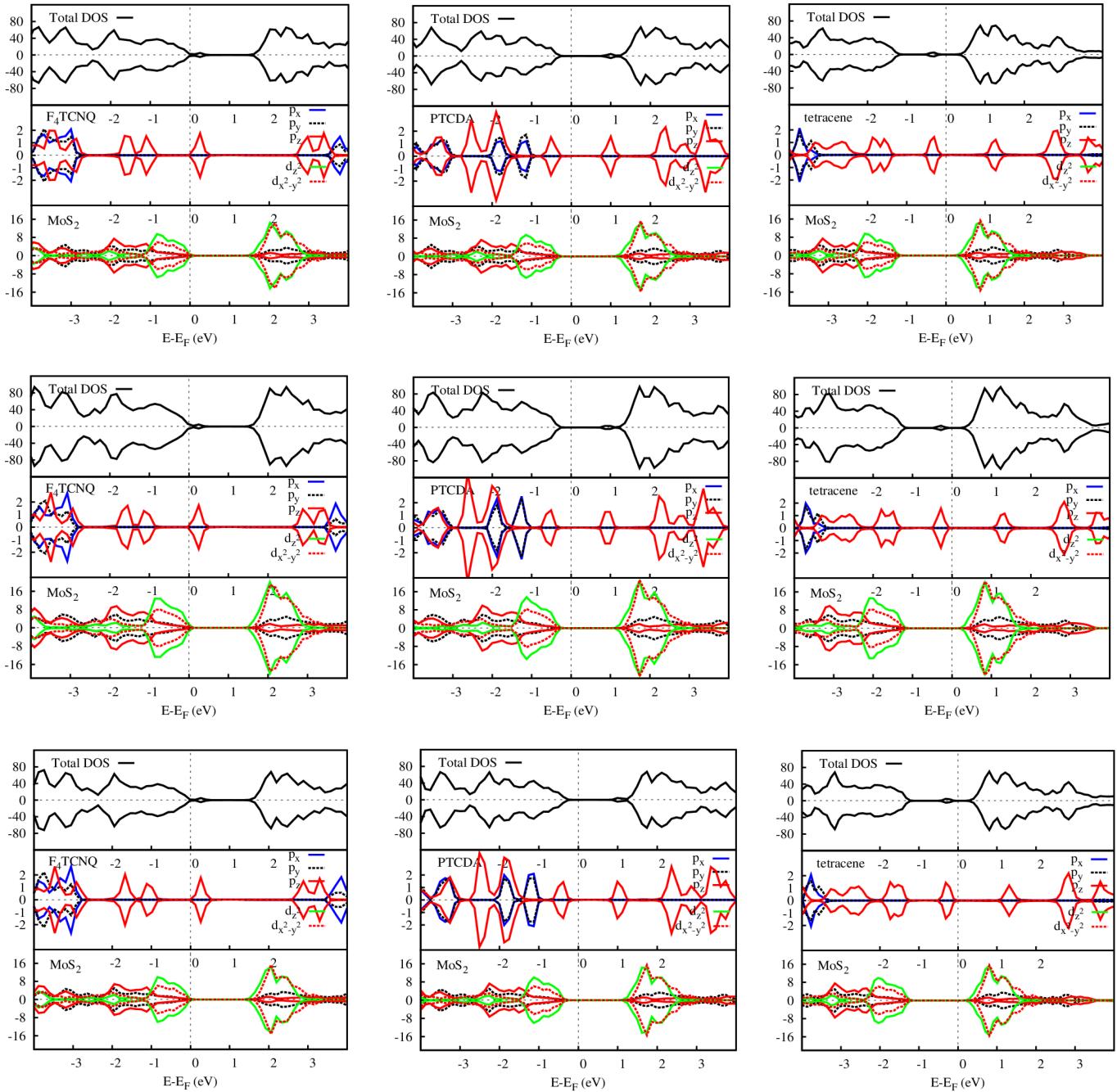


Fig. S3 From left to right, electronic density of states of $\text{MoS}_2/\text{F}_4\text{TCNQ}$, MoS_2PTCDA , and $\text{MoS}_2\text{/tetracene}$ with the parallel adsorption configuration. The first to third rows are those for the 5×5 unit cell, the 6×6 unit cell of the monolayer MoS_2 , and taking into account the van der Waals correction, respectively.